

# **HAT2189WP**

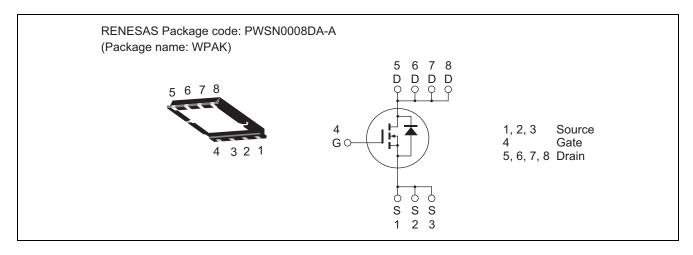
# Silicon N Channel Power MOS FET Power Switching

REJ03G1251-0200 Rev.2.00 Aug 28, 2009

### **Features**

- Low on-resistance
- Low drive current
- High density mounting

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	200	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub>	8.5	Α
Drain peak current	I <sub>D (pulse)</sub> Note1	17	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	8.5	Α
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	17	Α
Avalanche current	I <sub>AP</sub> Note3	8.5	Α
Avalanche energy	E <sub>AR</sub> Note3	4.8	mJ
Channel dissipation	Pch Note2	20	W
Channel to case thermal impedance	θch-c	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

3. STch = 25°C, Tch  $\leq$  150°C

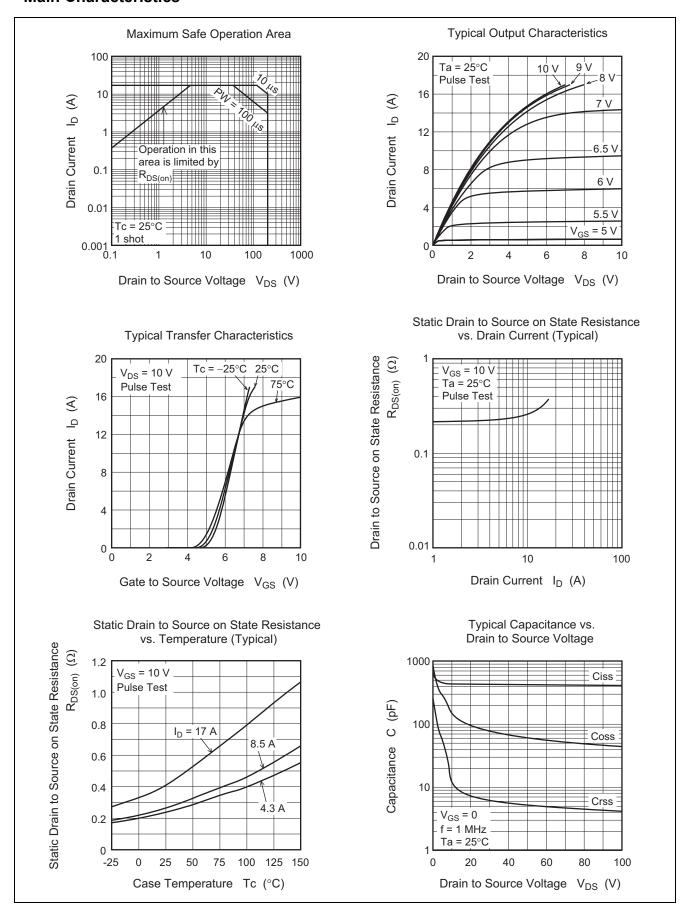
# **Electrical Characteristics**

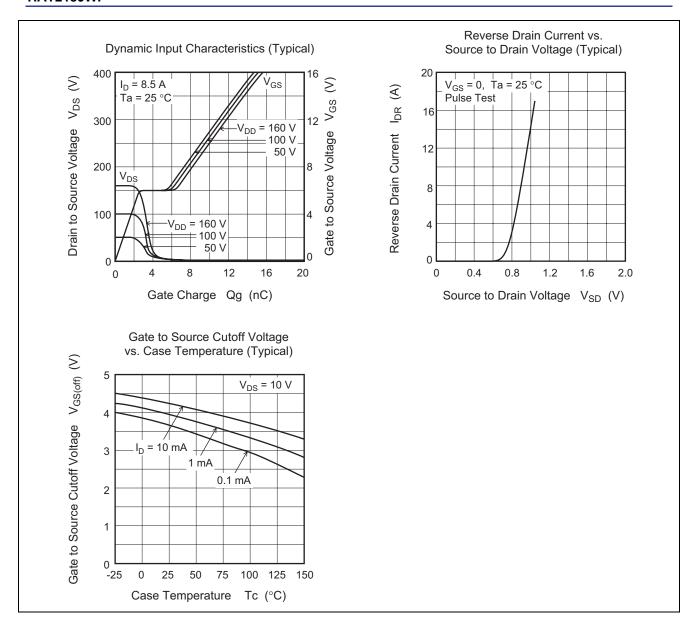
 $(Ta = 25^{\circ}C)$ 

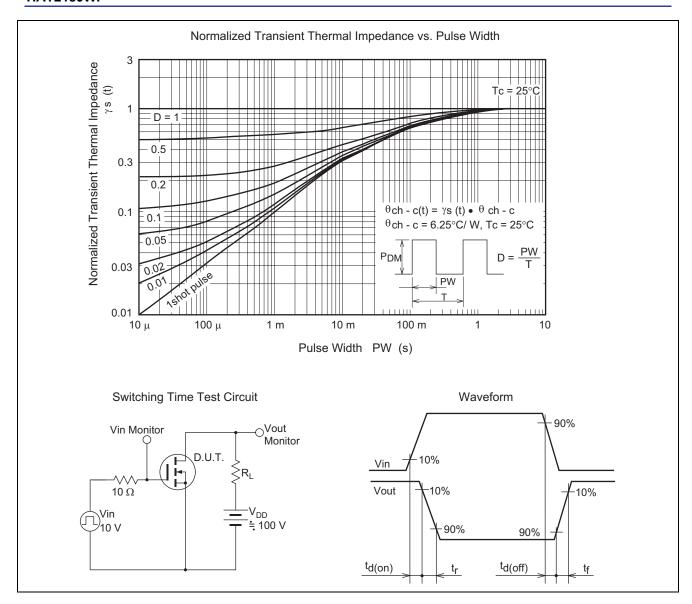
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y <sub>fs</sub>	3.5	6.0	_	S	$I_D = 4.3 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	0.23	0.27	Ω	$I_D = 4.3 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance						
Input capacitance	Ciss		430	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss		86	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	7	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	24	_	ns	I <sub>D</sub> = 4.3 A
Rise time	t <sub>r</sub>	_	24	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	44	_	ns	$R_L = 23.3 \Omega$
Fall time	t <sub>f</sub>	_	9	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	10	_	nC	V <sub>DD</sub> = 160 V
Gate to source charge	Qgs	_	2.7	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	3.8	_	nC	I <sub>D</sub> = 8.5 A
Body-drain diode forward voltage	$V_{DF}$	_	0.9	1.4	V	$I_F = 8.5 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	100	_	ns	I <sub>F</sub> = 8.5 A, V <sub>GS</sub> = 0
						di <sub>F</sub> /dt = 100 A/μs

Notes: 4. Pulse test

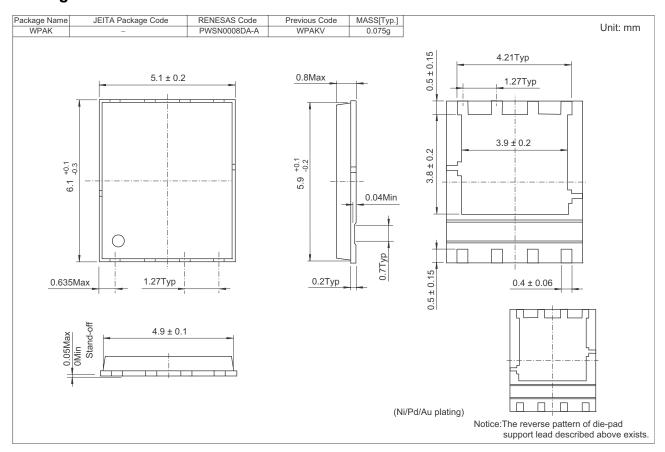
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2189WP-EL-E	2500 pcs	Taping

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